

Defect characterization of monocrystalline silicon solar cells with polysilicon passivated contact using electrically-detected magnetic resonance (EDMR) spectroscopy





Chirag Mule^{1,2}, David W. Mulder¹, Keiun Chen^{1,2}, William Nemeth¹, P. Craig Taylor², Dirk Stevn^{1,2}, Markus Kaupa¹, San Theingi¹, David Young¹, Sumit Agarwal², Pauls Stradins¹

¹National Renewable Energy Laboratory (NREL), USA. ²Colorado School of Mines (CSM), USA.

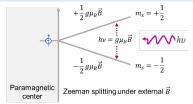
cmmule@mines.edu

Motivation

- · c-Si based solar cell efficiencies are approaching over 26%1,2
- · Critical to characterize the low concentration performance limiting defects - as low as 1010-1011 cm-3 (e.g., Fe contamination in GaCz Si3)
- · Atomistic level understanding of the mechanisms of the low-concentration process-induced-defects and reliability limiting defects is needed (e.g., LeTID)
- · Lifetime spectroscopies can still be used; however, they are based on estimations and theoretical models, and cannot fully reveal information about microscopic mechanisms.

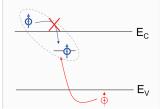
[1]. Lin, H. et al., Nat Energy (2023) doi:10.1038/s41560-023-01255-2 [2]. Richter, A. et al., Nat Energy 6, 429–438 (2021). [3]. Basnet, R. et al., Solar RRL (2023) doi:10.1002/solr.202300304.

Electrically detected magnetic resonance (EDMR) principle



- · Change in the cell output is due to change in the recombination at magnetic resonance condition.
- · EDMR is specific and sensitive to the performance affecting paramagnetic defects.

- ✓ Spin-polarization under external \vec{B}
- × No microwave radiation
- × No magnetic resonance
- × No spin flip
- × Transition permutation equilibrium (governed by spin-selection rules)



- ✓ Spin-polarization under external \vec{B}
- ✓ Microwave radiation ✓ Magnetic resonance
- Spin flip
- ✓ Transition permutation equilibrium gets shifted

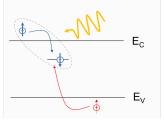


Fig. 1. (a) Zeeman-splitting; (b) Recombination under external \vec{B} ; (c) Change in recombination transitions at magnetic resonance condition.

Sample preparation

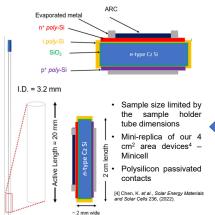
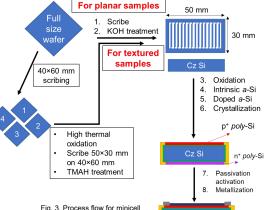


Fig. 2. (a) Cell-design; (b) Sample holder tube dimensions.

Results - Proof of concept EDMR

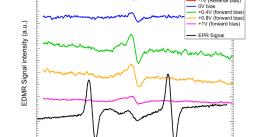
measurements at NREL

Minicell fabrication process flow



Cz Si

340



fabrication

332

Magnetic field (mT) Fig. 7. EDMR measurements at temperature ~5K varying the

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- a-value ~ 2.005 signal at likely due to the Si dangling bond inside the device at
- q-value ~ 1.998 signal at T~5K temperature shows bias dependency

Edge ablation damage removal for edge passivation

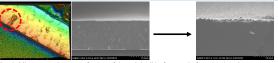


Fig. 4. Microscope images of edge of the minicell before and after ablation damage removal

Results - Proof of concept minicells

Sample ID	V _{oc} (V)	FF	J _{sc} (mA/cm²) (without ARC nitride)	Efficiency
Minicell-1	0.6494	74.8	25.62	12.4 %
Minicell-2	0.6598	74.7	26.24	12.9 %
4 cm ² device-1	0.6786	76.5	28.62	14.9 %
4 cm ² device-2	0.6842	76.5	28.46	14.9 %
Minicell-2 4 cm ² device-1	0.6598 0.6786	76.5	26.24 28.62	12.9 % 14.9 %



Performance of the minicells comparable to 4 cm2 devices fabricated simultaneously

Conclusion

- · We have shown proof of concept of minicell fabrication and EDMR measurement capability on them at NREL.
- We recorded EDMR signals at g-value ~2.005 and ~1.998 at different parameters, however, dependency of such parameters to study different recombination channels on the same device using EDMR needs to be understood properly.
- We aim to study some of the unknown defects in ongoing experiments.

Acknowledgement

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Fig. 6. EDMR measurements at temperature - 30K, 40K,

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Magnetic field (mT)

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50K. 80K. 100K.

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EDMR signal intensity (a.u.)